MY15G03E

30V N+P-Channel Complementary Mode MOSFET

General Description

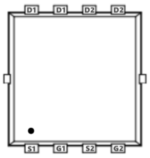
The MY15G03E is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications . The MY15G03E meet the RoHS and Green Product requirement 100% EAS guaranteed with full function eliability appoved.

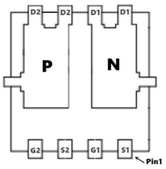
Features

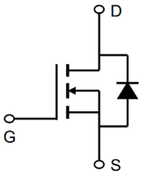
V_{DSS}	30	-30	V
I_D	16	-14	A
$R_{DS(ON)}$(atV_{GS}=10V)	10		mΩ
$R_{DS(ON)}$(atV_{GS}=4.5V)	15		mΩ
$R_{DS(ON)}$(atV_{GS}=-10V)	25		mΩ
$R_{DS(ON)}$(atV_{GS}=-4.5V)	30		mΩ

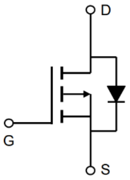
Application

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline









Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY15G03E	PDFN3*3-8L	MY15G03E	5000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	16	- 14	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	5	- 4	A
I_{DM}	Pulsed Drain Current[2]	40	-40	A
EAS	Single Pulse Avalanche Energy[3]	26.6	110	mJ
I_{AS}	Avalanche Current	8.7	-20	A
P_D@T_C=25℃	Total Power Dissipation[4]	10.8	10.8	W
P_D@T_A=25℃	Total Power Dissipation[4]	2	2	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	---	6	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.023	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	10	14	mΩ
		V_{GS}=4.5V , I_D=10A	---	15	21	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, I_D =250uA	1.0	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	14	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.3	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=10A	---	5	---	nC
Q_{gs}	Gate-Source Charge		---	1.11	---	
Q_{gd}	Gate-Drain Charge		---	2.61	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=12V , V_{GS}=10V , R_G=3.3Ω I_D=6A	---	7.7	---	ns
T_r	Rise Time		---	46	---	
$T_{d(off)}$	Turn-Off Delay Time		---	11	---	
T_f	Fall Time		---	3.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	416	---	pF
C_{oss}	Output Capacitance		---	62	---	
C_{rss}	Reverse Transfer Capacitance		---	51	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	$V_G=V_D$=0V , Force Current	---	---	16	A
I_{SM}	Pulsed Source Current[2,5]		---	---	30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=12.7A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.021	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-8A	---	25	30	mΩ
		V_{GS}=-4.5V , I_D=-6A	---	30	35	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	---	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-8A	---	12.6	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz		15	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-6A	---	9.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	3.4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-24V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	16.4	---	ns
T_r	Rise Time		---	20.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	930	---	pF
C_{oss}	Output Capacitance		---	148	---	
C_{rss}	Reverse Transfer Capacitance		---	115	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-14	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-24	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :
1. The data tested by surface mounted on a 1 $inch^2$ FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦300us , duty cycle≦2%
3. The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-30A
4. The power dissipation is limited by 150℃ junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

TYPICAL PERFORMANCE CHARACTERISTICS N-CHANNEL

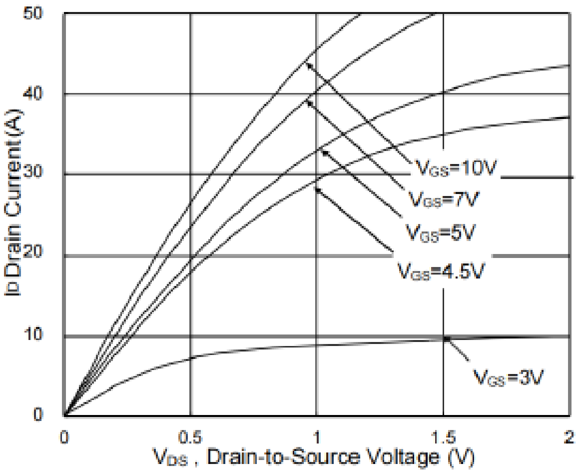


Fig.1 Typical Output Characteristics

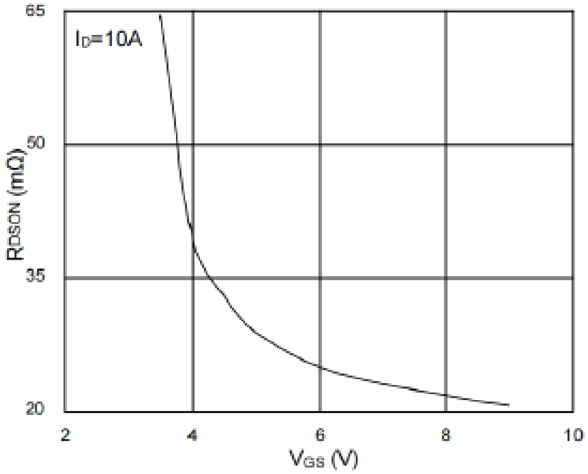


Fig.2 On-Resistance vs. Gate-Source

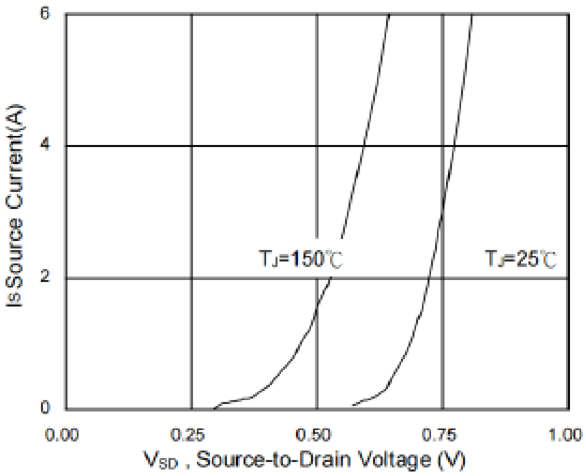


Fig.3 Forward Characteristics Of Reverse

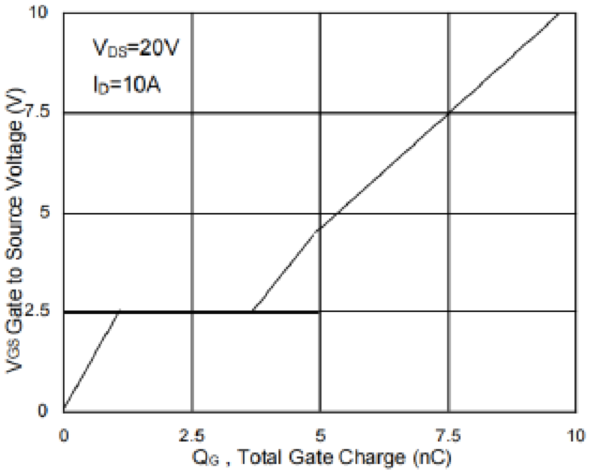


Fig.4 Gate-Charge Characteristics

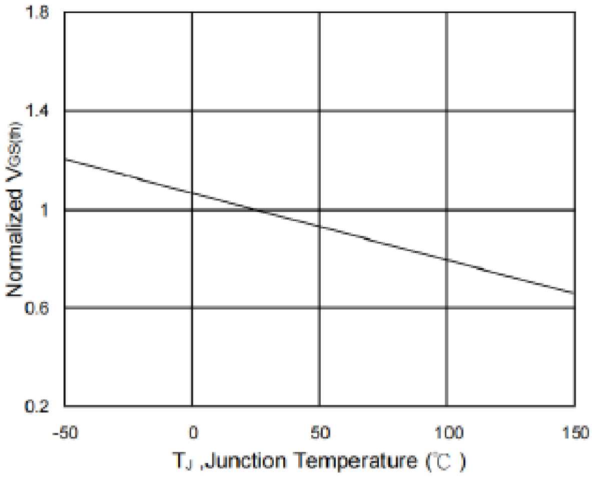


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

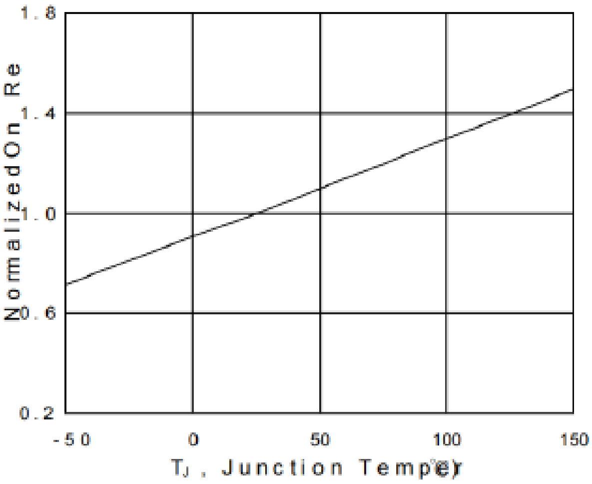
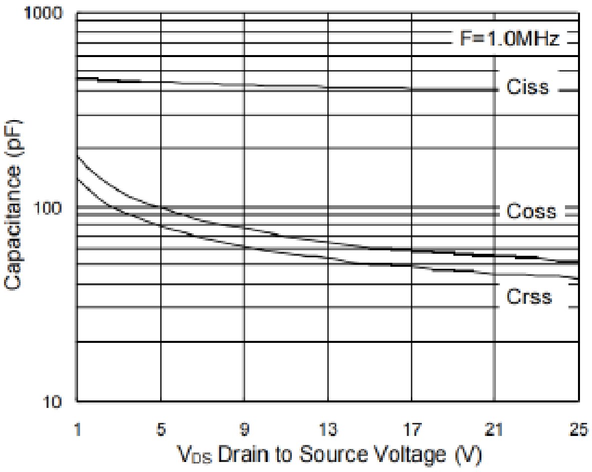


Fig.6 Normalized R_{DSON} vs. T_J



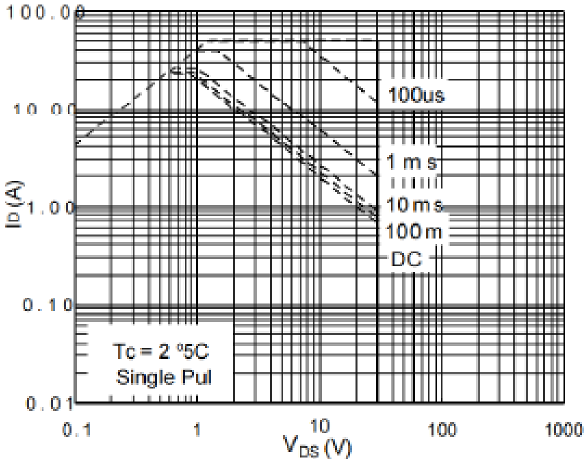


Fig.7 Capacitance

Fig.8 Safe Operating Area

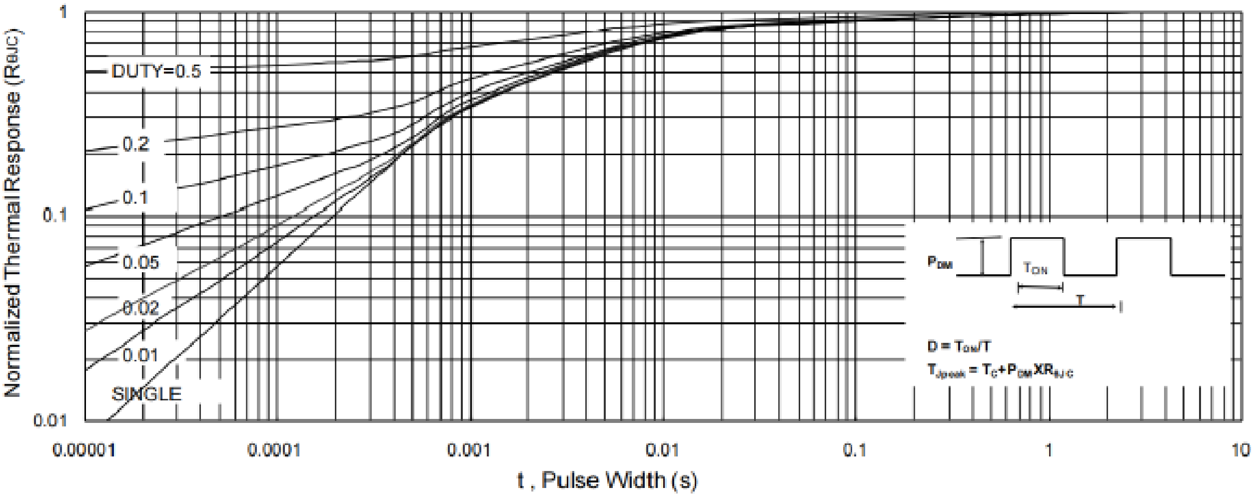
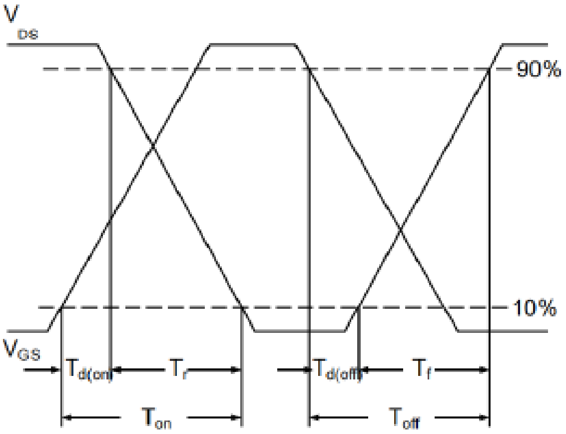
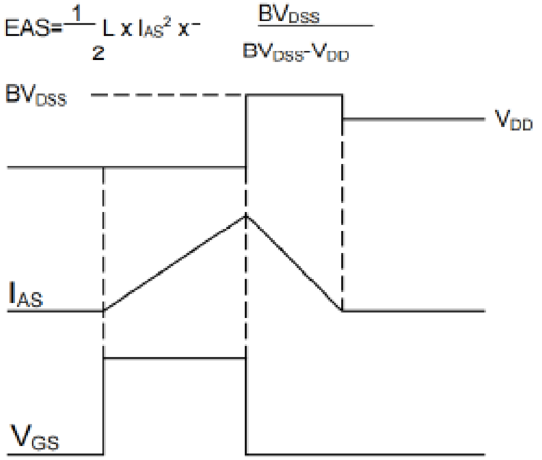


Fig.9 Normalized Maximum Transient Thermal Impedance





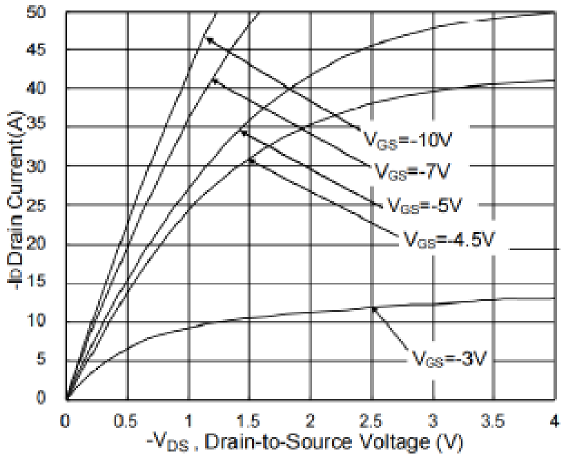


Fig.1 Typical Output Characteristics

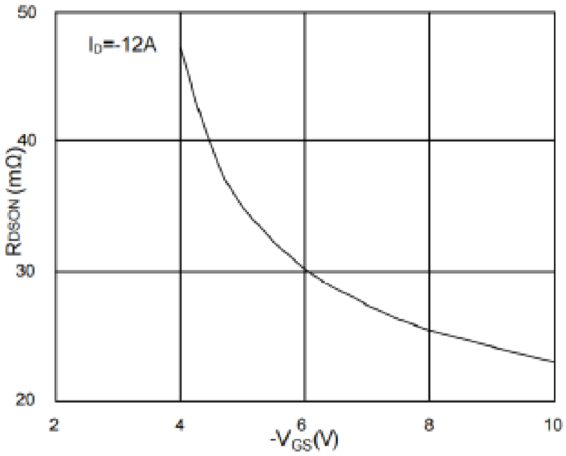


Fig.2 On-Resistance v.s Gate-Source

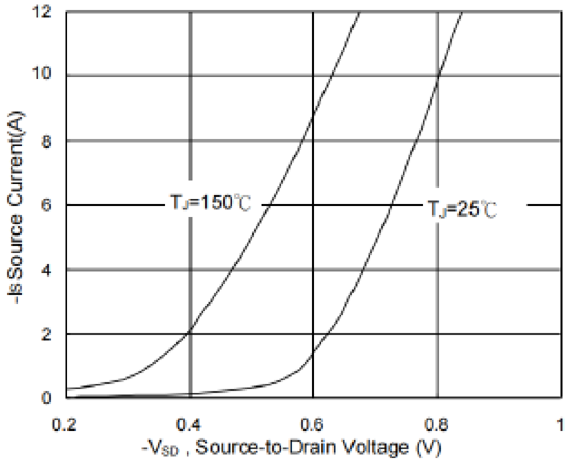


Fig.3 Forward Characteristics Of Reverse

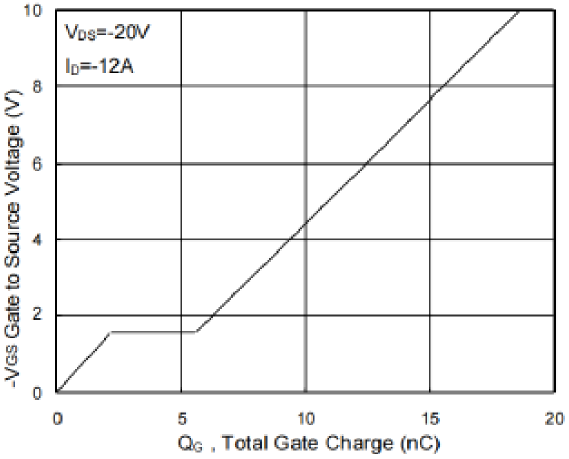


Fig.4 Gate-Charge Characteristics

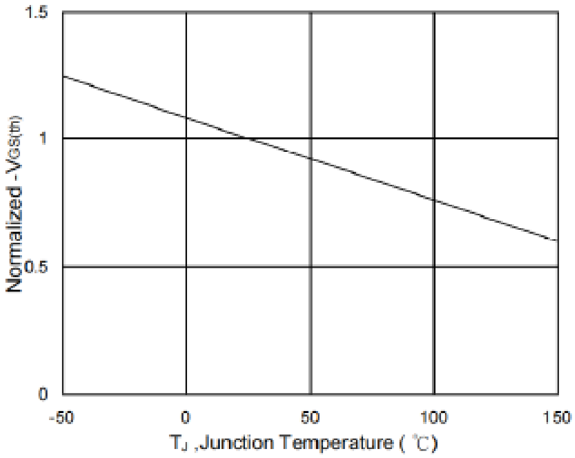


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

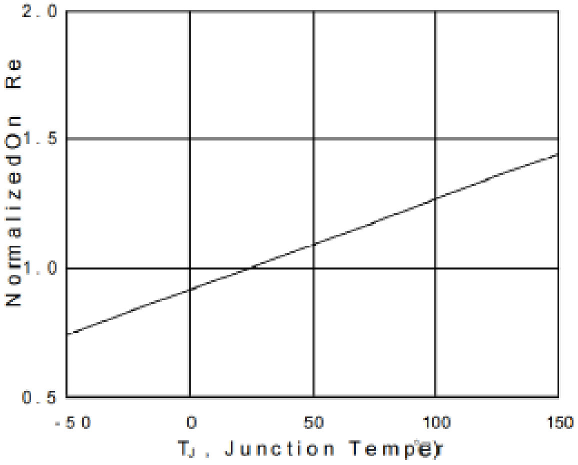


Fig.6 Normalized R_{DSON} v.s T_J

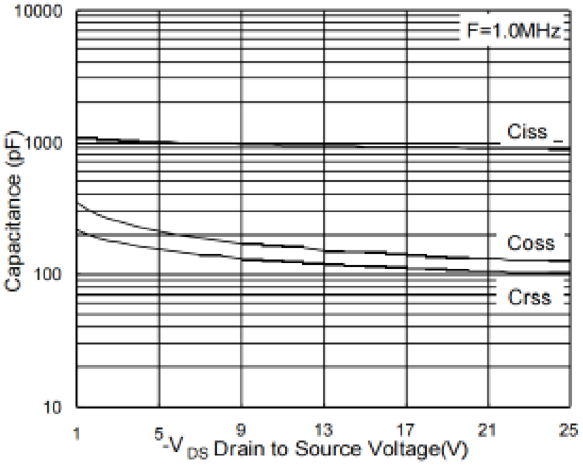


Fig.7 Capacitance

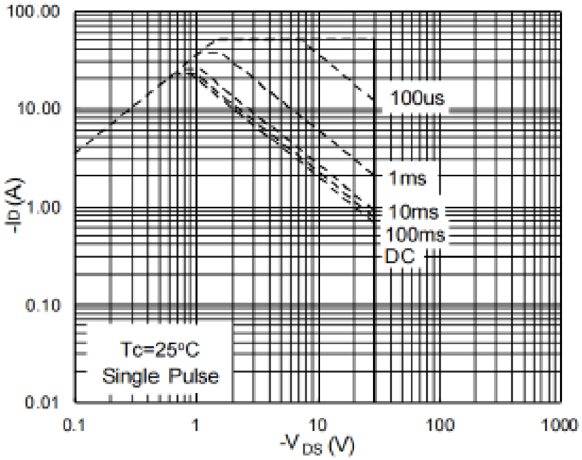


Fig.8 Safe Operating Area

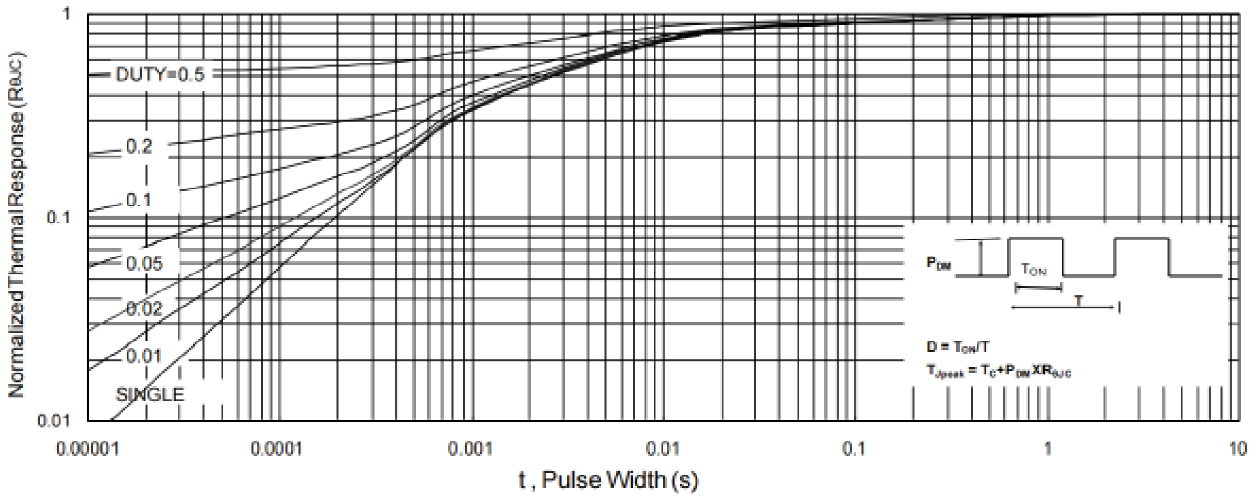


Fig.9 Normalized Maximum Transient Thermal Impedance

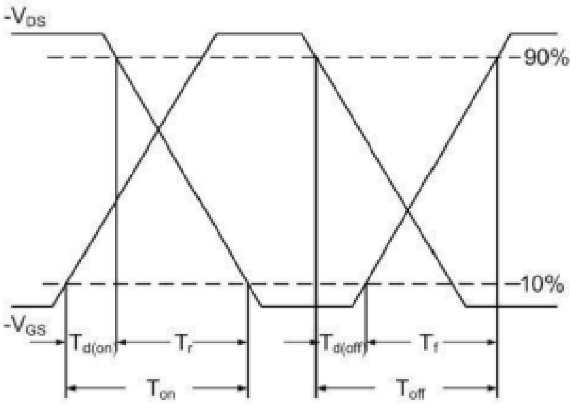


Fig.10 Switching Time Waveform

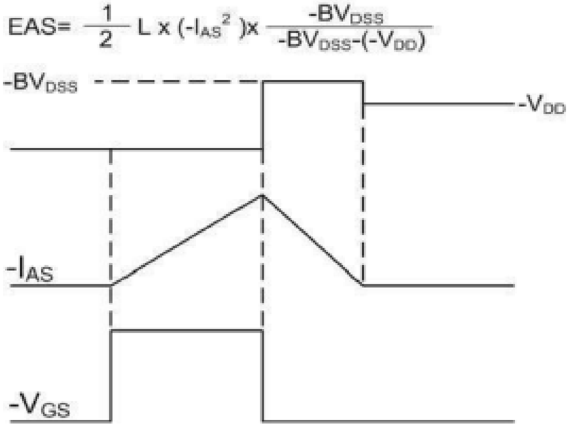
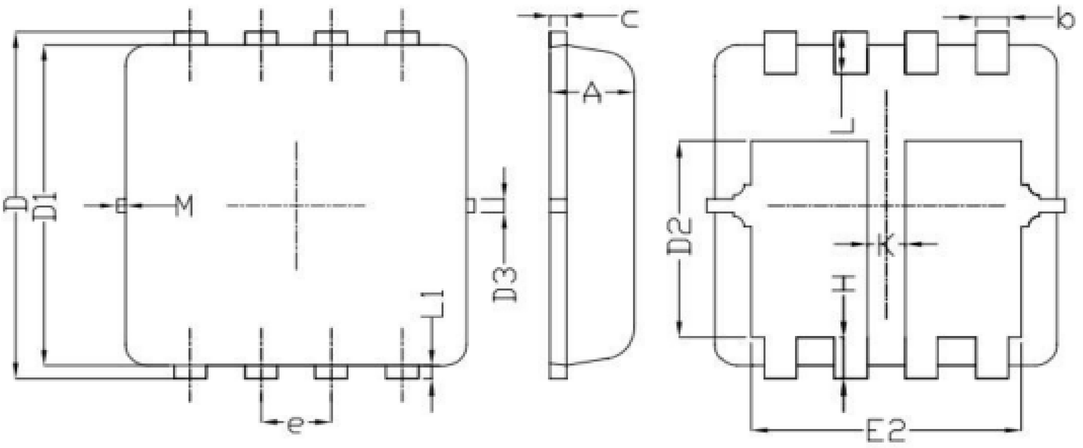
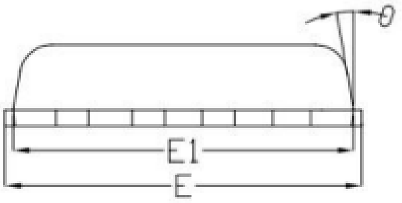
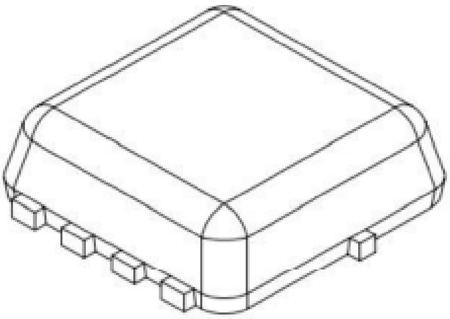


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-DFN3*3-8L-JQ Single







Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	--	0.13	--
K	0.30	--	--
θ	--	10°	12°
M	*	*	0.15
* Not Specified			

Notes:

1. Refer to JEDEC MO-240 variation CA.
2. Dimensions "D1" and "E1" do NOT include mold flash protrusions or gate burrs.
3. Dimensions "D1" and "E1" include interterminal flash or protrusion.